

Program of the Conference



VIII-th INTERNATIONAL CONFERENCE

Ion Implantation and Other Applications of Ions and Electrons

Kazimierz Dolny, Poland, June 14-17, 2010

Monday, June 14, 2010

10:00 - Registration

13:00 - Lunch

14:00	Opening of the Conference	
Afternoon session I		
14:15	L. Pranevičius (Lithuania)	Hydrogen separation under molecular ion implantation in nanocrystalline Mg films
14:45	J. Piekoszewski (Poland)	The effect of chromium on formation of nitrogen expanded austenite phase in Fe-Cr alloy induced by high intensity nitrogen pulses
15:15	A.D. Pogrebnjak (Ukraine)	Application of plasma jets for fabrication of coatings from metals, hard alloys, ceramics, and their combination
15:45	D.L. Alontseva (Kazakhstan)	The structural phase changes in Ni -Cr- and Co-Cr based coatings deposited by plasma detonation and the results of coatings' modification by duplex treatment

16:05 Coffee break

Afternoon session II		
16:30	M. Ali (Egypt)	The use of PIXE in evaluation of Coptic Wall Paintings conservation (case study)
16:50	A. Michel (France)	Interaction between energy of deposited species and intrinsic stress build-up in thin solid films grown by magnetron sputtering
17:20	P. Konarski (Poland)	Vacuum annealing effects in nickel alloys applied in aviation industry – Depth profile analysis by secondary ion mass spectrometry (SIMS) and glow discharge mass spectrometry (GDMS)
17:40	I. Józwick (Poland)	Thermal annealing of carbon layers formed via ion-beam induced hydrocarbons decomposition

18:00 Scientific Committee Meeting

19:15 Wellcome dinner

Tuesday, June 15, 2010

7:30÷8:30 Breakfast

Morning session I		
8:30	K. Potzger (Germany)	Ion-beam synthesis of magnetic semiconductors
9:00	A. Maziewski (Poland)	Tuning of ultrathin film magnetic properties by ions irradiation

9:30	A. Misiuk (Poland)	Properties of Si:V annealed under enhanced hydrostatic pressure
10:00	Z. Werner (Poland)	The effects of He irradiation in manganese implanted silicon
10:30	J. Fedotova (Belarus)	Magnetoresistance in n-Si/SiO ₂ /Ni nanostructures manufactured by swift heavy ion-induced modification technology

10:50 Coffee break

Morning session II

11:15	L. Thomé (France)	On the damage build-up in ion-irradiated ceramics
11:45	J. Jagielski (Poland)	Effect of grain size on mechanical properties of irradiated mono- and polycrystalline MgAl ₂ O ₄

12:15 – 14:00 **Poster Session I**

14:00 Lunch

Afternoon session III

15:00	J. Sullivan (United Kingdom)	Deposition and properties of ultra fast deposited diamond-like hydrogenated carbon films
15:30	G.M. Wu (Taiwan R.O.C.)	Aluminum-doped zinc oxide thin films prepared by sol-gel and RF magnetron sputtering
15:50	A. Turos (Poland)	Stopping power and energy straggling of channeled He-ions in GaN
16:10	W. Wierzchowski (Poland)	X-ray diffraction studies of strain distribution in 6H SiC repeatedly implanted with Al ions
16:40	G. Gawlik (Poland)	Ion and electron beam induced luminescence of rare earth doped YAG crystals
17:00	F. Nickel (Germany)	News about the precise numerical value of the fine structure constant
17:30	Z. Wroński (Poland)	Diagnostics of ion-cathode interaction of glow discharges

18:00 Dinner

19:30 Organ Concerto

Wednesday, June 16, 2010

7:30÷8:30 Breakfast

Young Scientist Contest (oral and poster)

8:30	K. Pałowska	RBS\channeling and TEM study of damage buildup in ion bombarded III-N compounds
8:50	A. Stępkowska (Poland)	Application of electron beam radiation to modify crosslink structure in rubber vulcanizates and its tribological consequences
9:10	O. Yastrubchak (Poland, Ukraine)	Application of the ion implantation for the synthesis and modification of the (Ga,Mn)As ferromagnetic semiconductors
9:30	S. Abd El Aal (Egypt)	Identification of painting layers Sennefer Tomb by ion beam analysis
9:50	J. Lehmann (Germany)	Wear-out phenomena in Si-based light emitting devices with ion beam implanted europium
10:10	M. Sochacki (Poland)	Reactive ion etching (RIE) of 4H-SiC in fluorinated plasma for device fabrication
10:30	S. Prucnal (Poland)	Optical and microstructural properties of In(As,N) quantum structure made by ion implantation and flash lamp processing
8:30÷10:50 Posters:		
	I. A. Chugrov	Effect of ion doping on optical properties

	(Russia)	of multilayered nc-Si/high-k-oxide structures
	A. Mikhaylov (Russia)	Ion-beam synthesis and modification of light-emitting silicon and silicon-carbon nanoclusters in oxide layers
	R. Ratajczak (Poland)	Defect transformations in ion bombarded InGaAsP
	V. Tsvyrko (Belarus)	Formation of H-donors and radiation defects in proton implanted SiGe

10:50 Coffee break

11:00 – 13:00 **Poster Session II**

13:00 Lunch

14:00 Excursion

20:00 Barbecue

Thursday, June 17, 2010

7:30-8:30 Breakfast

Morning session IV		
8:30	F.F. Komarov (Belarus)	Peculiarities of swift proton transmission through tapered glass capillaries
9:00	W. Skorupa (Germany)	Advances in Si & Ge millisecond processing: From silicon-on-insulator to superconducting Ge
9:30	B. Nycz (Poland)	Diagnostics of high intensity pulsed plasma beams by ex-post analysis of morphology of the irradiated silicon surface
9:50	R. Hurley (United Kingdom)	Hydrogen and helium implantation in germanium for semiconductor layer transfer applications
10:20	C. Cherkourk (Germany)	Estrogen detection in waterish solutions by silicon based light emitters

10:40 Coffee break

Morning session V		
11:00	B. Słowiński (Poland)	Space structure and fluctuation of electromagnetic cascades produced by 100-3500 MeV gamma quanta in heavy amorphous media
11:30	T. Wilczyńska (Poland)	The changes of manganin thermoresistance properties induced by Nb, Ti, C low energy and then Kr high energy ion implantation
11:50	M. Turek (Poland)	Plasma ion source with an internal evaporator
12:10	P. Szałański (Poland)	Analysis of the iron state in ferric and ferrous iron containing pharmaceutical products available in Poland by Mössbauer spectroscopy
12:30	Closing of the Conference	

13:00 Lunch

14:00 Departure